

# DATA SHEET

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**74LVC10**

Triple 3-input NAND gate

Product specification  
Replaces data sheet of 1996 Feb  
IC24 Data Handbook

1997 Apr 28

## Triple 3-input NAND gate

## 74LVC10

## FEATURES

- Wide supply voltage range of 1.2 V to 3.6 V
- In accordance with JEDEC standard no. 8-1A.
- Inputs accept voltages up to 5.5 V
- CMOS low power consumption
- Direct interface with TTL levels
- Output capability: standard
- $I_{CC}$  category: SSI

## DESCRIPTION

The 74LVC10 is a high performance, low power, low voltage, Si gate CMOS device and superior to most advanced CMOS compatible TTL families.

The 74LVC10 provides the 3-input NAND function.

## QUICK REFERENCE DATA

GND = 0 V;  $T_{amb} = 25^{\circ}\text{C}$ ;  $t_r = t_f \leq 2.5$  ns

SYMBOL	PARAMETER	CONDITIONS	TYPICAL	UNIT
$t_{PHL}/t_{PLH}$	Propagation delay nA, nB, nC to nY	$C_L = 50$ pF; $V_{CC} = 3.3$ V	3.9	ns
$C_I$	Input capacitance		5.0	pF
$C_{PD}$	Power dissipation capacitance per gate	$V_I = \text{GND to } V_{CC}^1$	26	pF

## NOTE:

1.  $C_{PD}$  is used to determine the dynamic power dissipation ( $P_D$  in  $\mu\text{W}$ )

$P_D = C_{PD} \times V_{CC}^2 \times f_i + \sum (C_L \times V_{CC}^2 \times f_o)$  where:

$f_i$  = input frequency in MHz;  $C_L$  = output load capacity in pF;

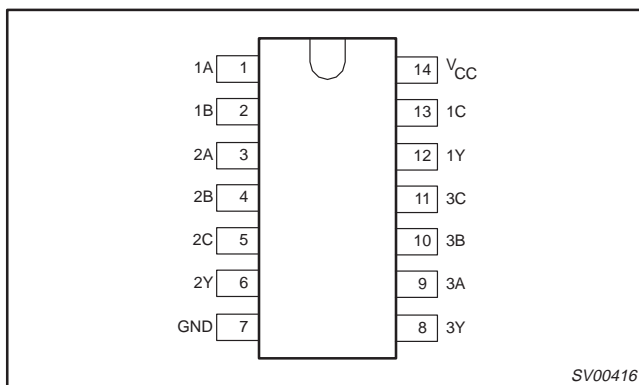
$f_o$  = output frequency in MHz;  $V_{CC}$  = supply voltage in V;

$\sum (C_L \times V_{CC}^2 \times f_o)$  = sum of the outputs.

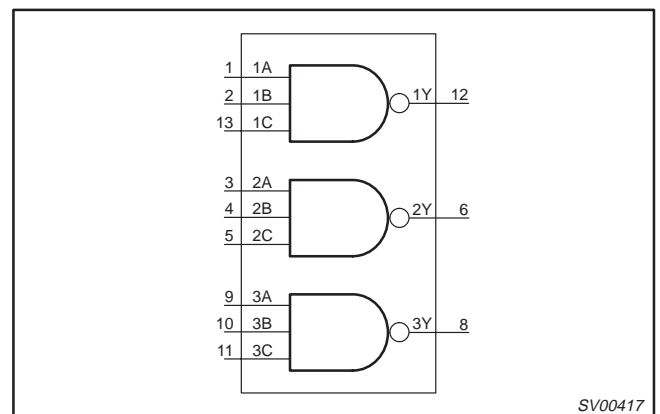
## ORDERING INFORMATION

PACKAGES	TEMPERATURE RANGE	OUTSIDE NORTH AMERICA	NORTH AMERICA	DWG NUMBER
14-Pin Plastic SO	$-40^{\circ}\text{C to } +85^{\circ}\text{C}$	74LVC10 D	74LVC10 D	SOT108-1
14-Pin Plastic SSOP Type II	$-40^{\circ}\text{C to } +85^{\circ}\text{C}$	74LVC10 DB	74LVC10 DB	SOT337-1
14-Pin Plastic TSSOP Type I	$-40^{\circ}\text{C to } +85^{\circ}\text{C}$	74LVC10 PW	74LVC10PW DH	SOT402-1

## PIN CONFIGURATION



## LOGIC SYMBOL



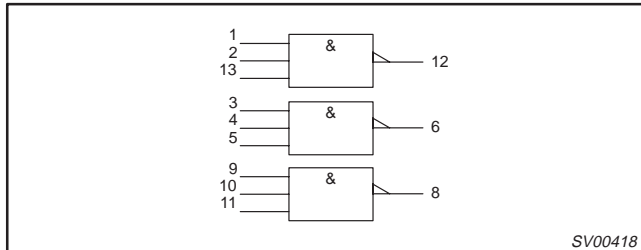
## PIN DESCRIPTION

PIN NUMBER	SYMBOL	NAME AND FUNCTION
1, 3, 9	1A – 3A	Data inputs
2, 4, 10	1B – 3B	Data inputs
7	GND	Ground (0 V)
12, 6, 8	1Y – 3Y	Data outputs
13, 5, 11	1C – 3C	Data inputs
14	$V_{CC}$	Positive supply voltage

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## LOGIC SYMBOL (IEEE/IEC)



## FUNCTION TABLE

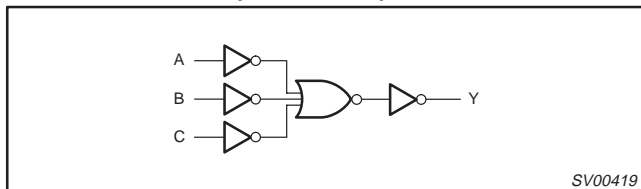
INPUTS			OUTPUTS
nA	nB	nC	nY
L	L	L	H
L	L	H	H
L	H	L	H
L	H	H	H
H	L	L	H
H	L	H	H
H	H	L	H
H	H	H	L

## NOTES:

H = HIGH voltage level

L = LOW voltage level

## LOGIC DIAGRAM (ONE GATE)



## RECOMMENDED OPERATING CONDITIONS

SYMBOL	PARAMETER	CONDITIONS	LIMITS		UNIT
			MIN	MAX	
$V_{CC}$	DC supply voltage (for max. speed performance)		2.7	3.6	V
$V_{CC}$	DC supply voltage (for low-voltage applications)		1.2	3.6	V
$V_I$	DC input voltage range		0	5.5	V
$V_{I/O}$	DC input voltage range for I/Os		0	$V_{CC}$	V
$V_O$	DC output voltage range		0	$V_{CC}$	V
$T_{amb}$	Operating free-air temperature range		-40	+85	°C
$t_r, t_f$	Input rise and fall times	$V_{CC} = 1.2$ to $2.7V$ $V_{CC} = 2.7$ to $3.6V$	0	20 10	ns/V

ABSOLUTE MAXIMUM RATINGS<sup>1</sup>

In accordance with the Absolute Maximum Rating System (IEC 134).

Voltages are referenced to GND (ground = 0V).

SYMBOL	PARAMETER	CONDITIONS	RATING	UNIT
$V_{CC}$	DC supply voltage		-0.5 to +6.5	V
$I_{IK}$	DC input diode current	$V_I < 0$	-50	mA
$V_I$	DC input voltage	Note 2	-0.5 to +5.5	V
$V_{I/O}$	DC input voltage range for I/Os		-0.5 to $V_{CC} + 0.5$	V
$I_{OK}$	DC output diode current	$V_O > V_{CC}$ or $V_O < 0$	±50	mA
$V_{OUT}$	DC output voltage	Note 2	-0.5 to $V_{CC} + 0.5$	V
$I_{OUT}$	DC output source or sink current	$V_O = 0$ to $V_{CC}$	±50	mA
$I_{GND}, I_{CC}$	DC $V_{CC}$ or GND current		±100	mA
$T_{stg}$	Storage temperature range		-60 to +150	°C
$P_{TOT}$	Power dissipation per package – plastic mini-pack (SO) – plastic shrink mini-pack (SSOP and TSSOP)	above +70°C derate linearly with 8 mW/K above +60°C derate linearly with 5.5 mW/K	500 500	mW

## NOTES:

- Stresses beyond those listed may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

# Triple 3-input NAND gate

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## DC ELECTRICAL CHARACTERISTICS

Over recommended operating conditions. Voltages are referenced to GND (ground = 0V).

SYMBOL	PARAMETER	TEST CONDITIONS	LIMITS			UNIT
			Temp = -40°C to +85°C			
			MIN	TYP <sup>1</sup>	MAX	
V <sub>IH</sub>	HIGH level Input voltage	V <sub>CC</sub> = 1.2V	V <sub>CC</sub>			V
		V <sub>CC</sub> = 2.7 to 3.6V	2.0			
V <sub>IL</sub>	LOW level Input voltage	V <sub>CC</sub> = 1.2V			GND	V
		V <sub>CC</sub> = 2.7 to 3.6V			0.8	
V <sub>OH</sub>	HIGH level output voltage	V <sub>CC</sub> = 2.7V; V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub> ; I <sub>O</sub> = -12mA	V <sub>CC</sub> - 0.5			V
		V <sub>CC</sub> = 3.0V; V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub> ; I <sub>O</sub> = -100µA	V <sub>CC</sub> - 0.2	V <sub>CC</sub>		
		V <sub>CC</sub> = 3.0V; V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub> ; I <sub>O</sub> = -12mA	V <sub>CC</sub> - 0.6			
		V <sub>CC</sub> = 3.0V; V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub> ; I <sub>O</sub> = -24mA	V <sub>CC</sub> - 1.0			
V <sub>OL</sub>	LOW level output voltage	V <sub>CC</sub> = 2.7V; V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub> ; I <sub>O</sub> = 12mA			0.40	V
		V <sub>CC</sub> = 3.0V; V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub> ; I <sub>O</sub> = 100µA			0.20	
		V <sub>CC</sub> = 3.0V; V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub> ; I <sub>O</sub> = 24mA			0.55	
I <sub>I</sub>	Input leakage current	V <sub>CC</sub> = 3.6V; V <sub>I</sub> = 5.5V or GND; Not for I/O pins		±0.1	±5	µA
I <sub>IHZ</sub> /I <sub>ILZ</sub>	Input current for common I/O pins	V <sub>CC</sub> = 3.6V; V <sub>I</sub> = V <sub>CC</sub> or GND		±0.1	±15	µA
I <sub>OZ</sub>	3-State output OFF-state current	V <sub>CC</sub> = 3.6V; V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub> ; V <sub>O</sub> = V <sub>CC</sub> or GND		0.1	±10	µA
I <sub>CC</sub>	Quiescent supply current	V <sub>CC</sub> = 3.6V; V <sub>I</sub> = V <sub>CC</sub> or GND; I <sub>O</sub> = 0		0.1	20	µA
ΔI <sub>CC</sub>	Additional quiescent supply current per input pin	V <sub>CC</sub> = 2.7V to 3.6V; V <sub>I</sub> = V <sub>CC</sub> - 0.6V; I <sub>O</sub> = 0		5	500	µA

**NOTE:**

1. All typical values are at V<sub>CC</sub> = 3.3V and T<sub>amb</sub> = 25°C.

## AC CHARACTERISTICS

GND = 0 V; t<sub>r</sub> = t<sub>f</sub> ≤ 2.5 ns; C<sub>L</sub> = 50 pF

SYMBOL	PARAMETER	WAVEFORM	LIMITS						UNIT
			V <sub>CC</sub> = 3.3V ±0.3V			V <sub>CC</sub> = 2.7V		V <sub>CC</sub> = 1.2V	
			MIN	TYP <sup>1</sup>	MAX	MIN	MAX	TYP	
t <sub>PHL</sub> / t <sub>PLH</sub>	Propagation delay nA, nB, nC to nY	Figures 1, 2	-	3.9	6.4	-	7.5	-	ns

**NOTE:**

1. These typical values are at V<sub>CC</sub> = 3.3V and T<sub>amb</sub> = 25°C.

## AC WAVEFORMS

V<sub>M</sub> = 1.5 V at V<sub>CC</sub> ≥ 2.7 V

V<sub>M</sub> = 0.5 • V<sub>CC</sub> at V<sub>CC</sub> < 2.7 V

V<sub>OL</sub> and V<sub>OH</sub> are the typical output voltage drop that occur with the output load.

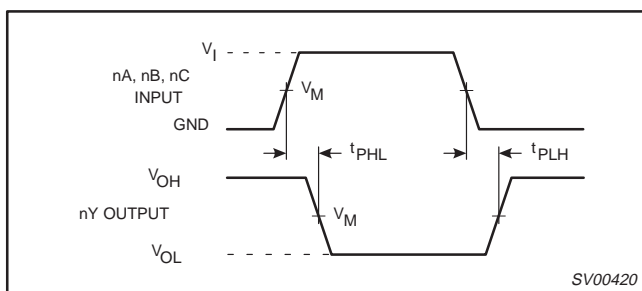


Figure 1. Input (nA, nB, nC) to output (nY) propagation delays.

## TEST CIRCUIT

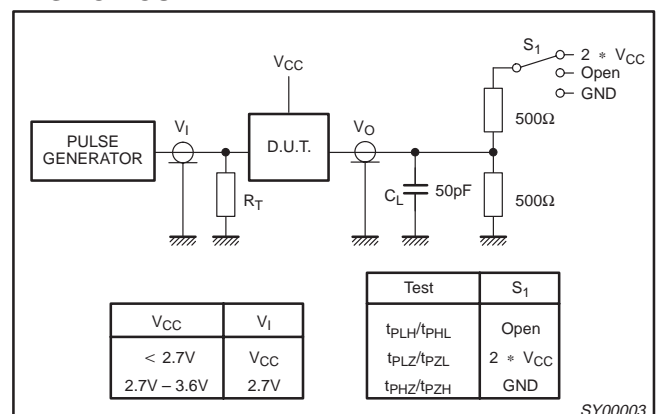


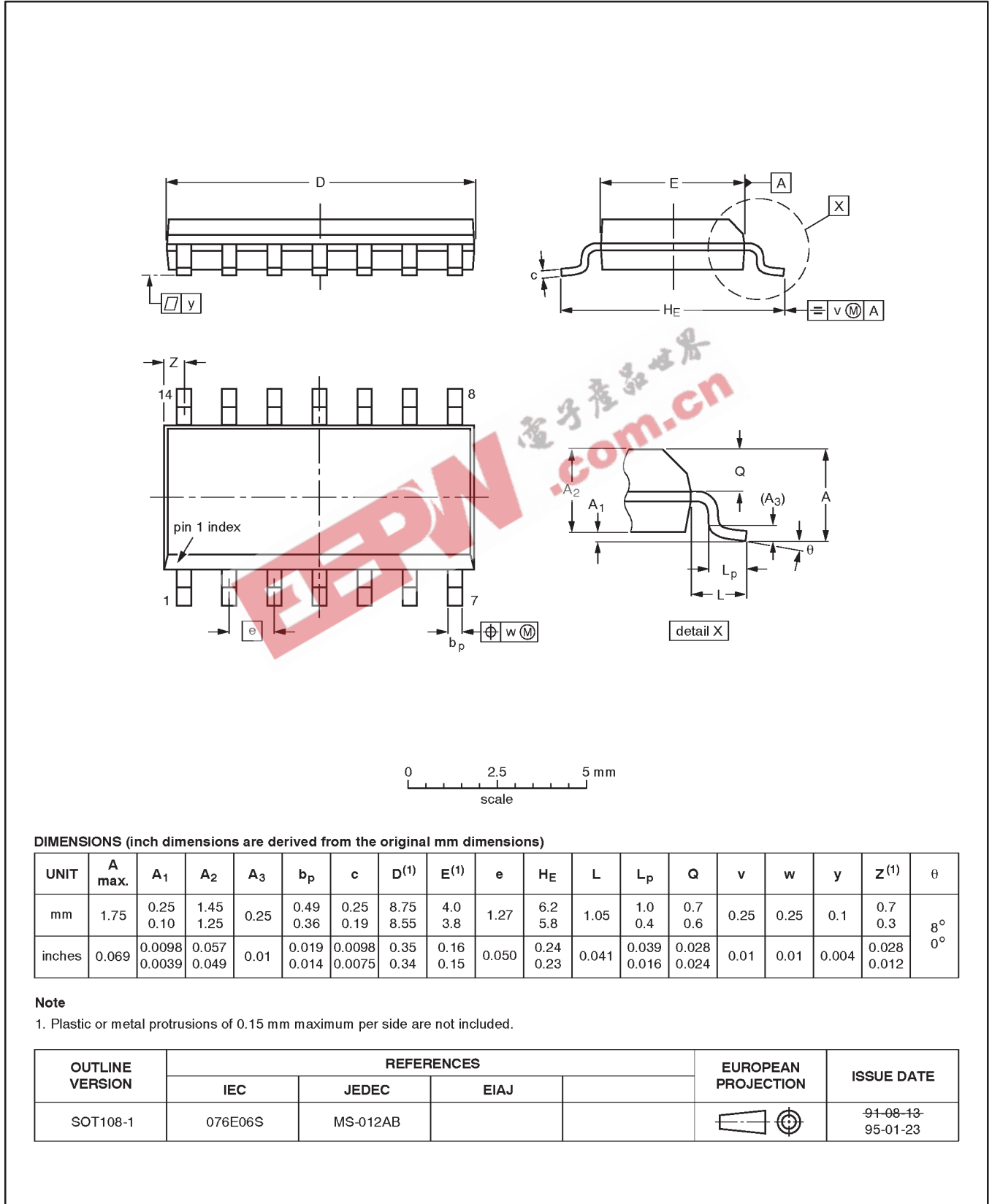
Figure 2. Load circuitry for switching times.

Triple 3-input NAND gate

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SO14: plastic small outline package; 14 leads; body width 3.9 mm

SOT108-1



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A <sub>1</sub>	A <sub>2</sub>	A <sub>3</sub>	b <sub>p</sub>	c	D <sup>(1)</sup>	E <sup>(1)</sup>	e	H <sub>E</sub>	L	L <sub>p</sub>	Q	v	w	y	z <sup>(1)</sup>	θ
mm	1.75	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	8.75 8.55	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8° 0°
inches	0.069	0.0098 0.0039	0.057 0.049	0.01	0.019 0.014	0.0098 0.0075	0.35 0.34	0.16 0.15	0.050	0.24 0.23	0.041	0.039 0.016	0.028 0.024	0.01	0.01	0.004	0.028 0.012	

Note

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

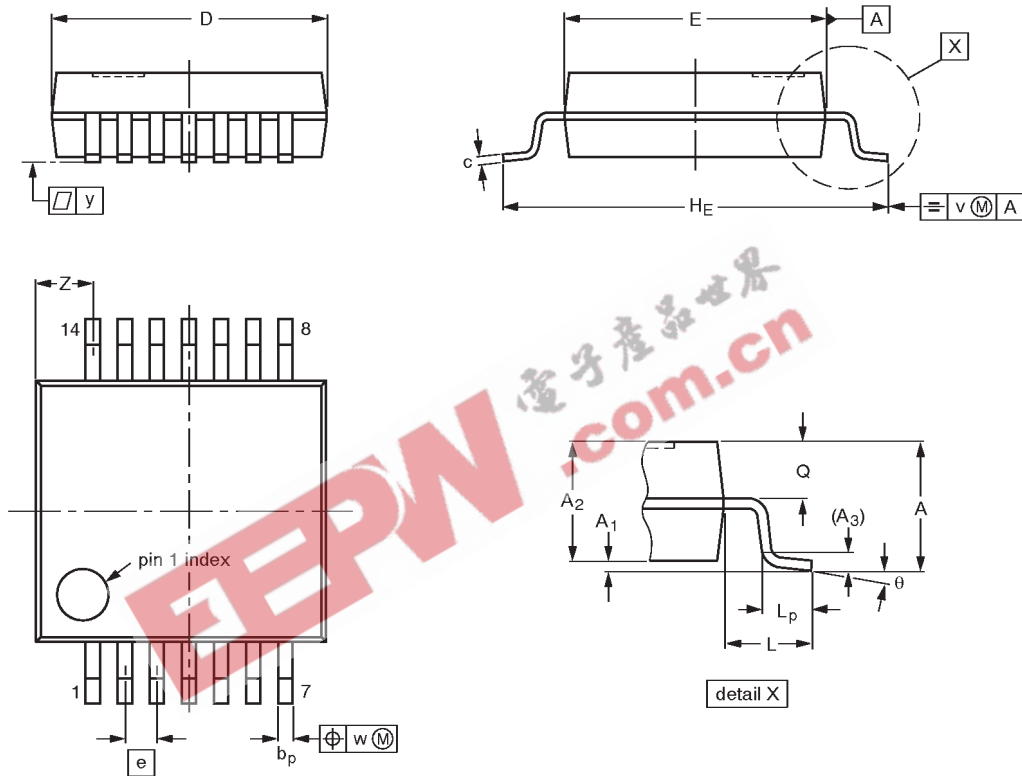
OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT108-1	076E06S	MS-012AB				91-08-13 95-01-23

Triple 3-input NAND gate

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SSOP14: plastic shrink small outline package; 14 leads; body width 5.3 mm

SOT337-1



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A <sub>1</sub>	A <sub>2</sub>	A <sub>3</sub>	b <sub>p</sub>	c	D <sup>(1)</sup>	E <sup>(1)</sup>	e	H <sub>E</sub>	L	L <sub>p</sub>	Q	v	w	y	Z <sup>(1)</sup>	θ
mm	2.0	0.21 0.05	1.80 1.65	0.25	0.38 0.25	0.20 0.09	6.4 6.0	5.4 5.2	0.65	7.9 7.6	1.25	1.03 0.63	0.9 0.7	0.2	0.13	0.1	1.4 0.9	8° 0°

Note

1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

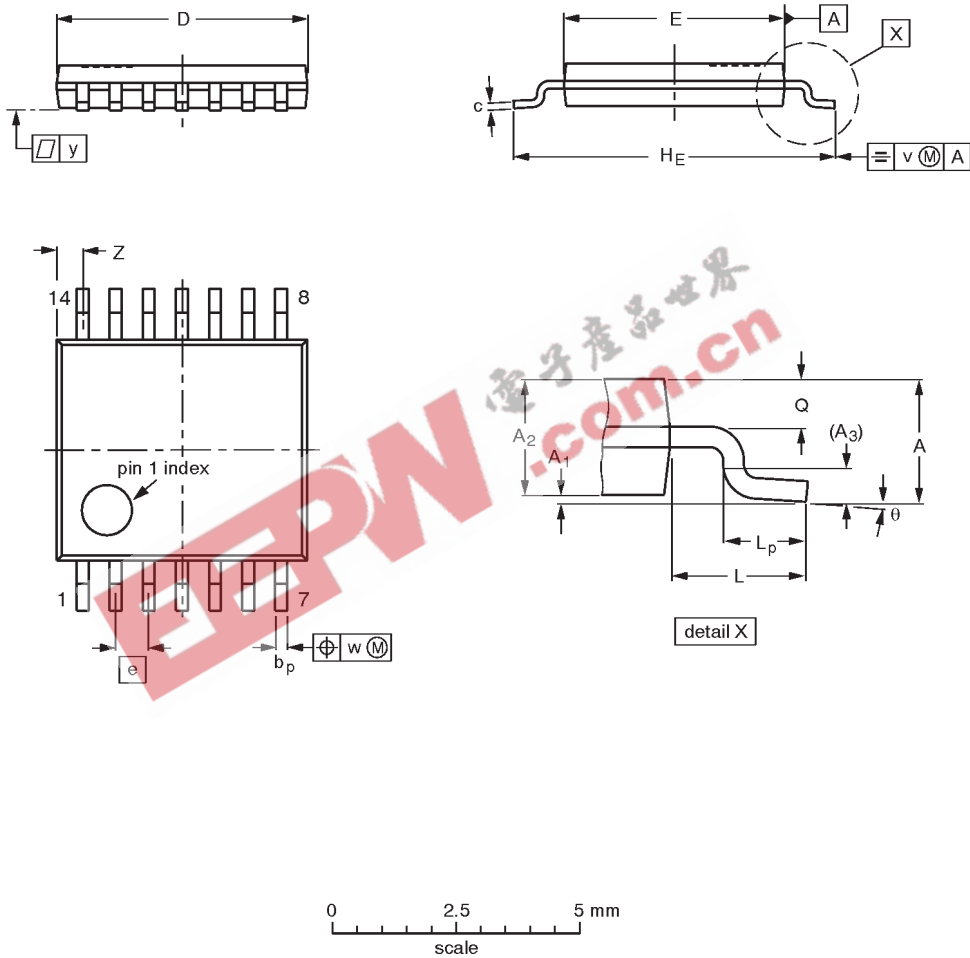
OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT337-1		MO-150AB				<del>95-02-04</del> 96-01-18

Triple 3-input NAND gate

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TSSOP14: plastic thin shrink small outline package; 14 leads; body width 4.4 mm

SOT402-1



**DIMENSIONS (mm are the original dimensions)**

UNIT	A max.	A <sub>1</sub>	A <sub>2</sub>	A <sub>3</sub>	b <sub>p</sub>	c	D <sup>(1)</sup>	E <sup>(2)</sup>	e	H <sub>E</sub>	L	L <sub>p</sub>	Q	v	w	y	Z <sup>(1)</sup>	θ
mm	1.10	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	5.1 4.9	4.5 4.3	0.65	6.6 6.2	1.0	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.72 0.38	8° 0°

**Notes**

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT402-1		MO-153				-94-07-12- 95-04-04

## Triple 3-input NAND gate

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## DEFINITIONS

Data Sheet Identification	Product Status	Definition
<i>Objective Specification</i>	<b>Formative or in Design</b>	This data sheet contains the design target or goal specifications for product development. Specifications may change in any manner without notice.
<i>Preliminary Specification</i>	<b>Preproduction Product</b>	This data sheet contains preliminary data, and supplementary data will be published at a later date. Philips Semiconductors reserves the right to make changes at any time without notice in order to improve design and supply the best possible product.
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